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|---|-----|---|---|---------------------|
| - | 182 | ((amorphizing amorphization amorphized amorphous) with (ion implant implantation implanting implanted) and ((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (recrystal crystal crystallize crystallization crystallizing recrystallize recrystallization recrystallizing anneal annealing annealling annealed) with (amorphized amorphous))) not (((amorphizing amorphization amorphized) with (trench groove recess recessed grooved)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/18 11:33 |
| - | 140 | amorphizing amorphization amorphized amorphous) with (ion implant implantation implanting implanted) and ((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (recrystal crystal crystallize crystallization crystallizing recrystallize recrystallization recrystallizing anneal annealing annealling annealed) with (amorphized amorphous))) not (((amorphizing amorphization amorphized) with (trench groove recess recessed grooved)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/18 15:42 |
| - | 0 | amorphizing amorphization amorphized amorphous) with (ion implant implantation implanting implanted) and ((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (recrystal crystal crystallize crystallization crystallizing recrystallize recrystallization recrystallizing anneal annealing annealling annealed) with (amorphized amorphous))) not (((amorphizing amorphization amorphized) with (trench groove recess recessed grooved)) | USPAT | 2003/06/18 14:05 |
| - | 10 | amorphizing amorphization amorphized amorphous) with (ion implant implantation implanting implanted) and ((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (recrystal crystal crystallize crystallization crystallizing recrystallize recrystallization recrystallizing anneal annealing annealling annealed) with (amorphized amorphous))) not (((amorphizing amorphization amorphized) with (trench groove recess recessed grooved)) | USPAT | 2003/06/18 14:05 |
| - | 554 | trench with DRAM with isolation | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/18 15:45 |
| - | 7 | (trench with DRAM with isolation) and conformal near (insulator oxide dioxide) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/18 15:43 |
| - | 4 | (trench with DRAM with isolation) and conformal near (insulator oxide dioxide) with trench | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/18 15:44 |
| - | 170 | trench with DRAM with sti | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/18 15:45 |
| - | 8 | trench with DRAM near2 sti | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/18 15:46 |
| - | 53 | trench with DRAM near4 sti not (trench with DRAM near2 sti) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/18 15:47 |
| - | 18 | trench with DRAM and conformal near2 (silicon near oxide) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/18 15:48 |

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| - | 6 | trench with DRAM and conformal near2 (silicon near oxide) with trench | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/18 15:48 |
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